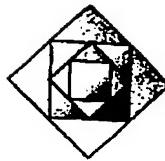


Appendix A

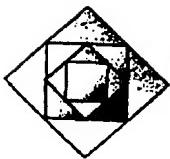
10/091,934



IBM

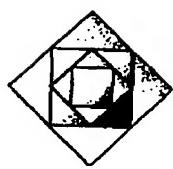
On-Chip Transmission Lines for
High Speed SiGe Applications:
Hardware verification status

Autodesk 2004



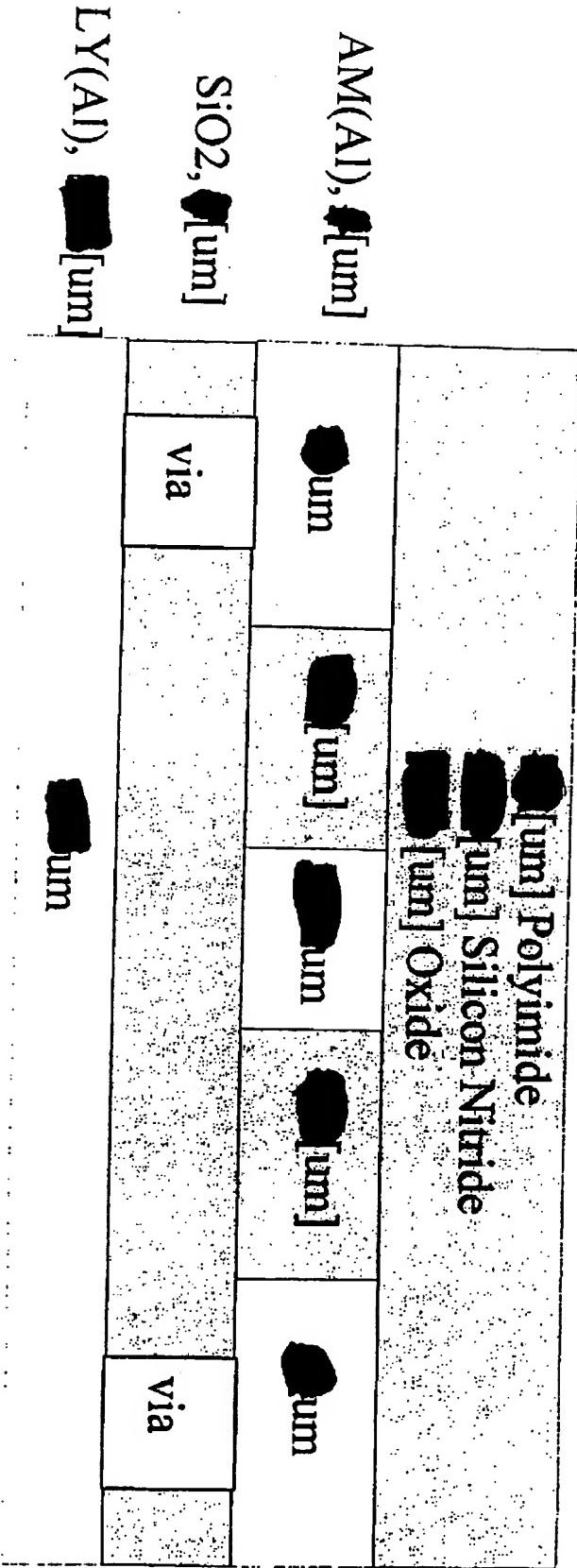
Outline

- Studied geometries
- Measurement setup
- EM solver calculation procedure
- IBM T-line model simulation
- SiGe [redacted] technology statistical variation
- Measurement results and EM solver correlation
- Alpha version (January 2001) model vs. measurement
- Beta version (August 2001) model vs. measurement
- Summary & conclusions

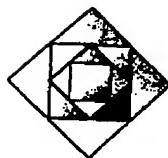


Sample No. 1

Single ~50 Ohm Transmission Line
Length=1025[um]

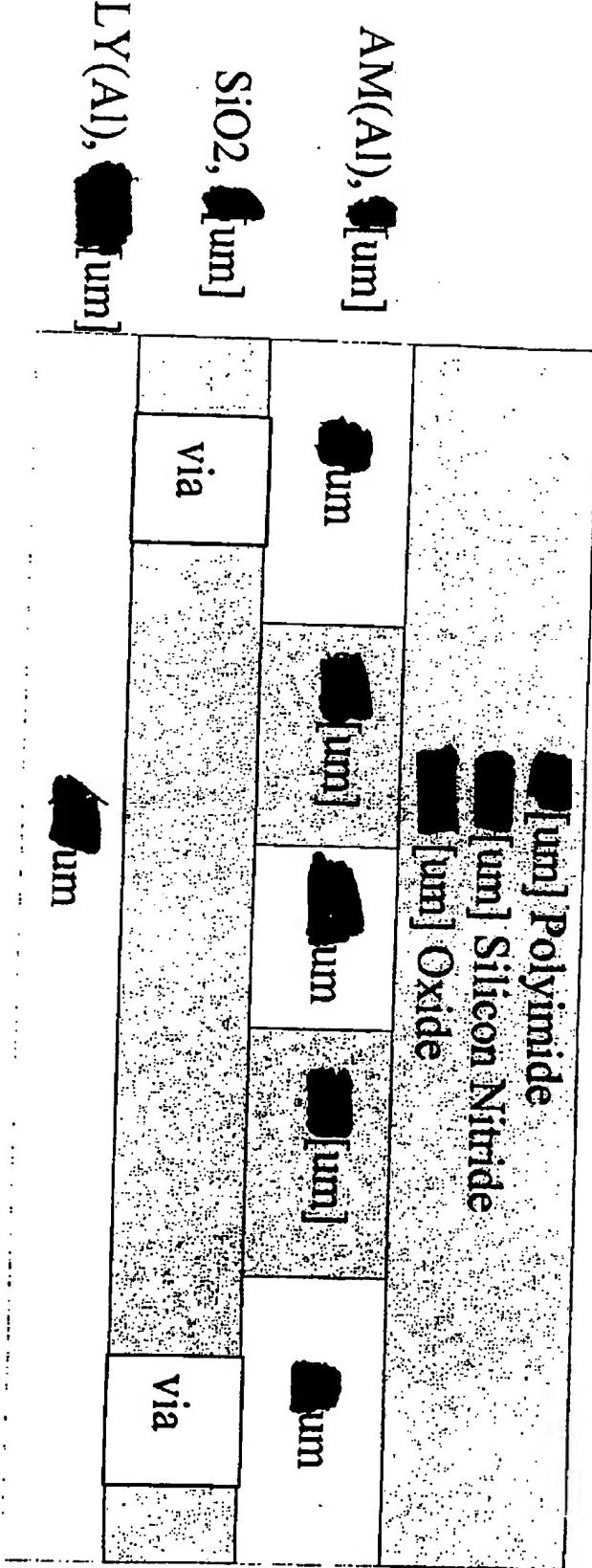


probing S/G pad: shielded AM/MT 30[um]X50[um]
Vias present only at both ends of T-line

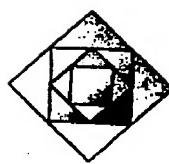


Sample No. 2

Single ~50 Ohm Transmission Line
Length=4010[um]

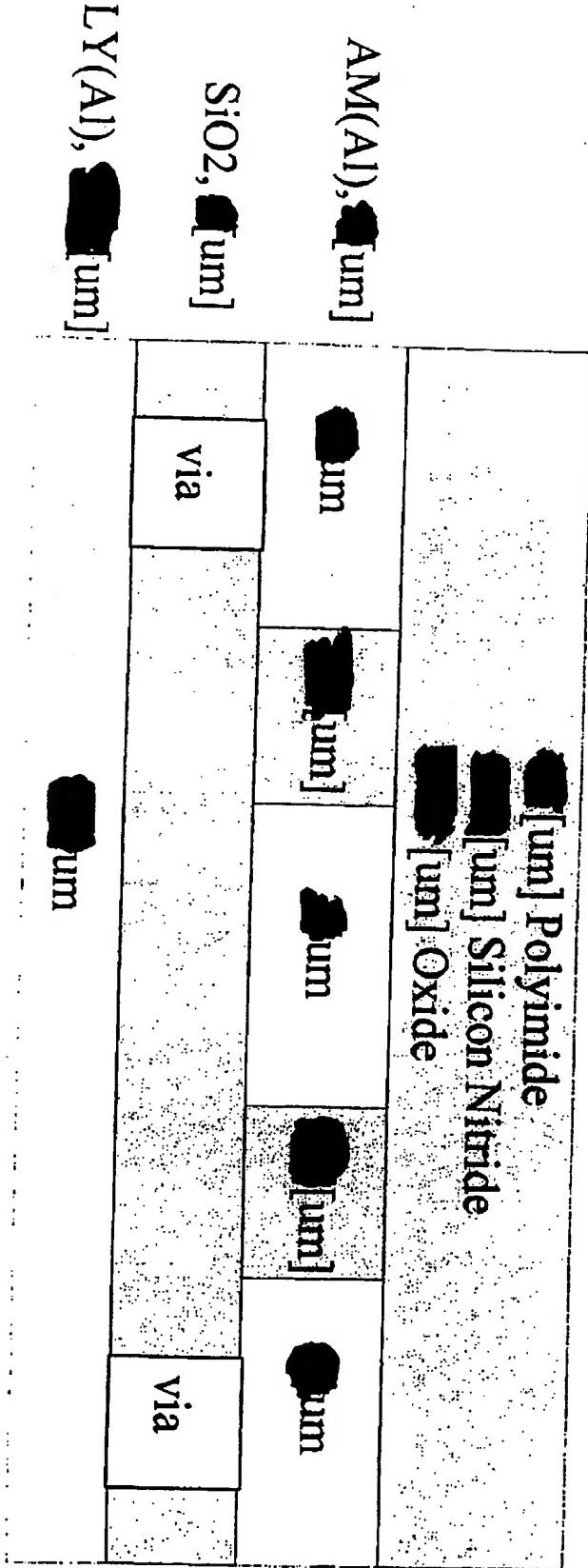


probing S/G pad: shielded AM/MT 30[um]X50[um]
Vias present only at both ends of T-line

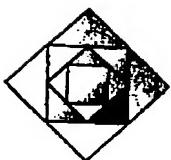


Sample No. 3

Single ~25 Ohm Transmission Line
Length=4010[um]



probing S/G pad: shielded AM/MT 30[um]X50[um]
Vias present only at both ends of T-line



Hardware measurement

Setup

- Two port measurement by 8510C Agilent 40[GHz] Vector Network Analyzer.

- Standard 40[GHz] RF coaxial cables.

- Wafer probes: [REDACTED] coplanar probes, GSG structure, beryllium copper tips (properly cleaned).

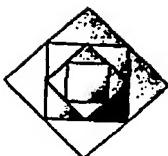
- Calibration procedure:

- ▶ LRRM type, using WinCal software.

- ▶ Cascade standard Alumina calibration substrate.

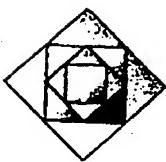
- ▶ On chip de-embedding by open pad structure, and Y-Parameter subtraction.

- ▶ Calibration error: residual tip inductance ~ 10[μ H], contact resistance ~ 0.1[Ohm], residual pad capacitance ~5[fF].



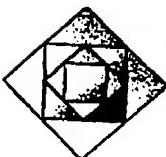
EM solver calculation procedure

- Start from Ansoft SI2D quasistatic 2D solver
(cross sectional dimensions are ~ 0.1% of 40[GHz] equivalent wavelength)
- Impedance mode calculates EM fields inside the metals (full eddy current solution).
- Verify RLC static limits accuracy using Ansoft EM2D.
- Verify asymptotic inductance values (L_{∞}) from basic physics relations.
- Perform mathematical conversion to 50[Ohm] based S - Parameters data.
- Verified against HFSS (with solve in metal option). Zero order interpolation (and patience...) is required with HFSS at the low frequency range.



IBM T-line model simulation

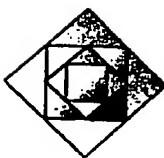
- IBM T-line models were simulated in [REDACTED] environment using the SPECTRES simulator.
- Simulation in S-Parameter mode.
- Two port simulation, with ideal 50[Ohm] ports.
- For the 4[mm] lines, four 1[mm] T-line models were connected in cascade.
- S-parameter data exported directly from SPECTRES and plotted versus the measured data.



SiGe technology statistical variation

Based on SiGe Design Manual data:

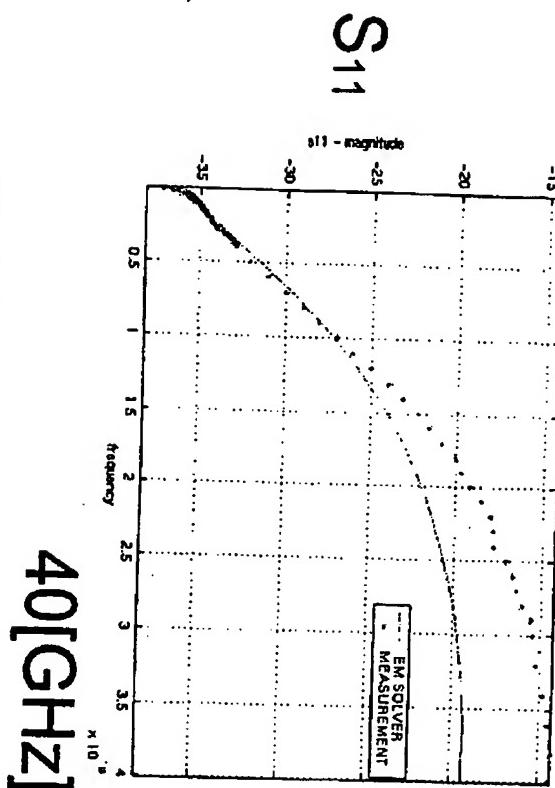
- Metal Line width, Metal line thickness, and SiO₂ dielectric thickness combined variations lead to $\sim \pm 10\%$ error in T-line capacitance and T-line inductance values (chip to chip variation).
- Same reasons lead to $\sim \pm 10\%$ error in T-line impedance values (chip to chip).
- T-line resistance variation is $\sim \pm 20\%$ (chip to chip).



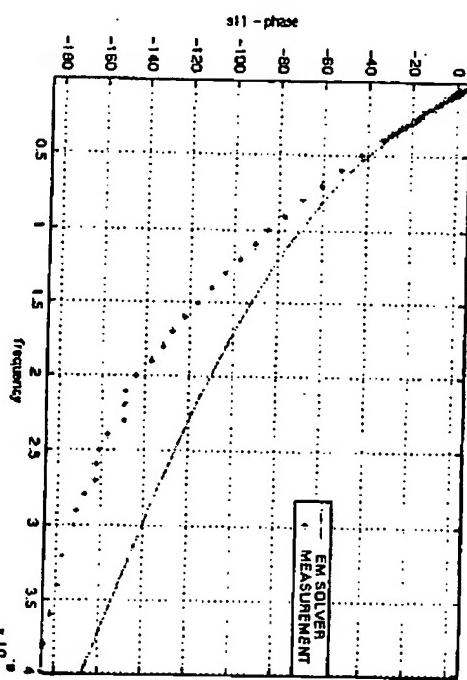
Hardware vs. Solver: Sample 1

$Z_0 \sim 50\text{[Ohm]}$, Length $\sim 1\text{[mm]}$

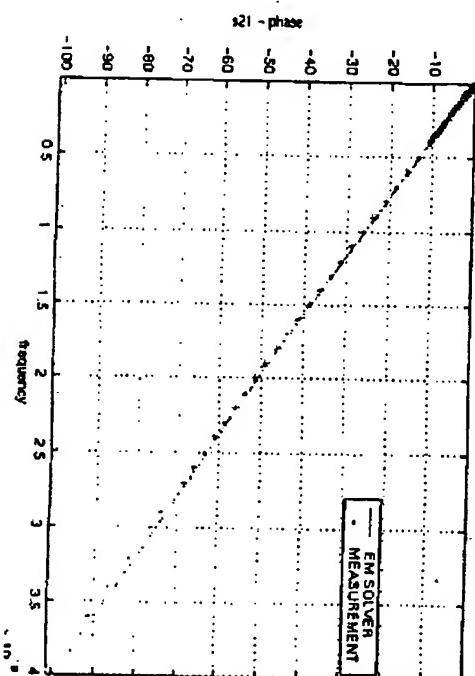
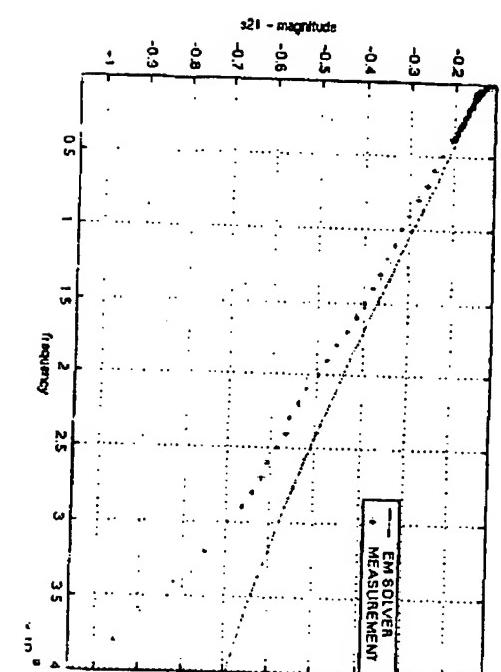
Magnitude [db]
Phase[degrees]



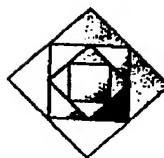
40[GHz]



40[GHz]



10

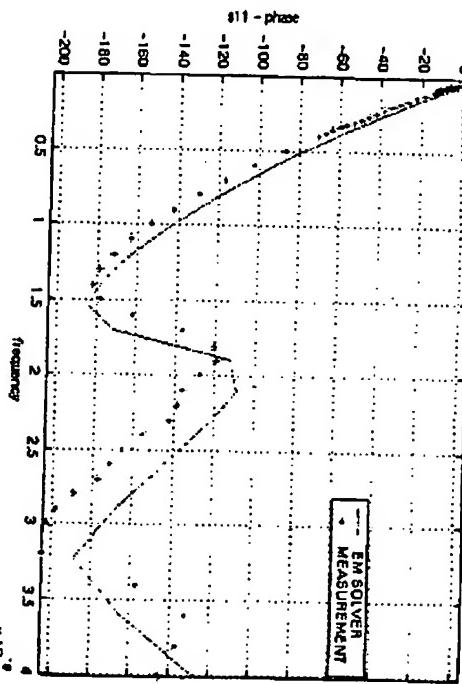


Hardware vs. Solver: Sample 2

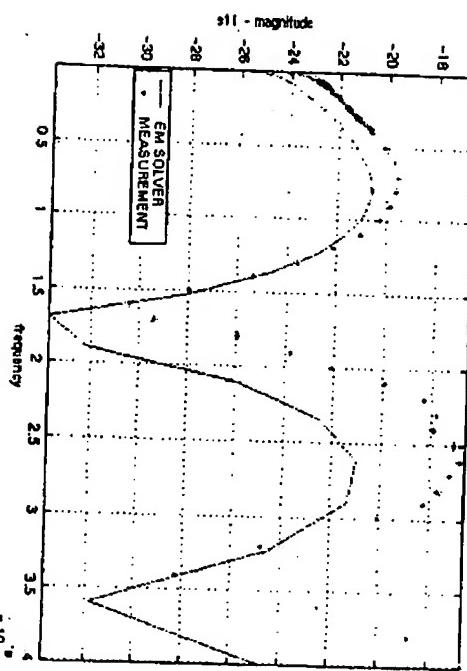
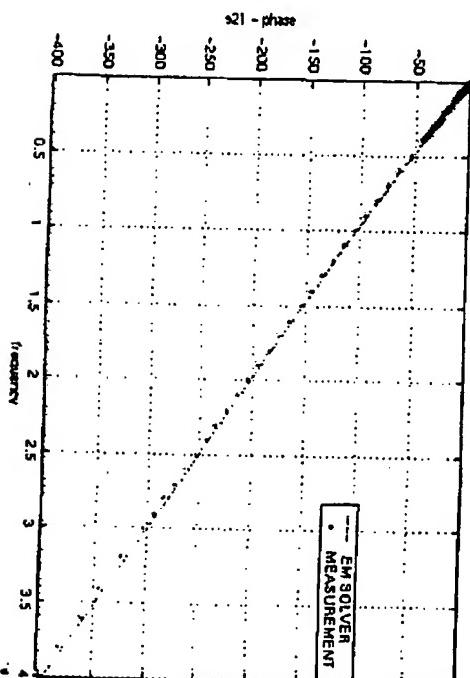
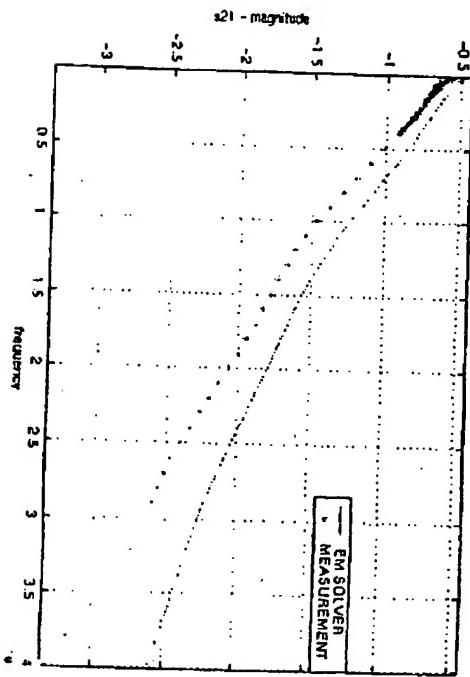
$Z_0 \sim 50 \text{ [Ohm]}, \text{ Length} \sim 4[\text{mm}]$

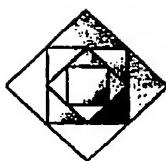
Magnitude [db] Phase[degrees]

40[GHz]



40[GHz]

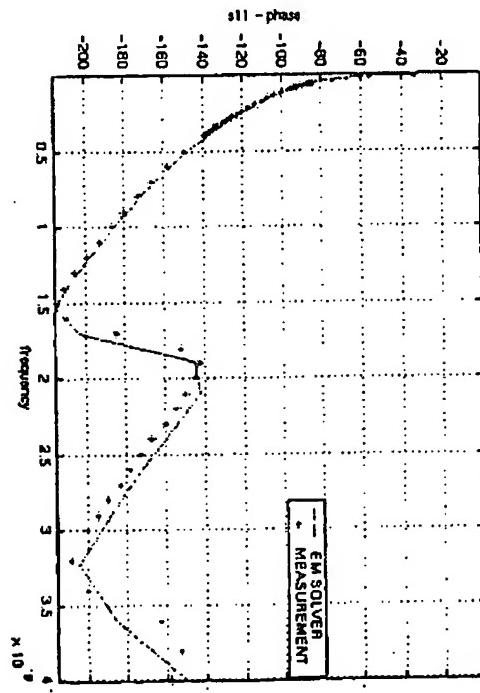
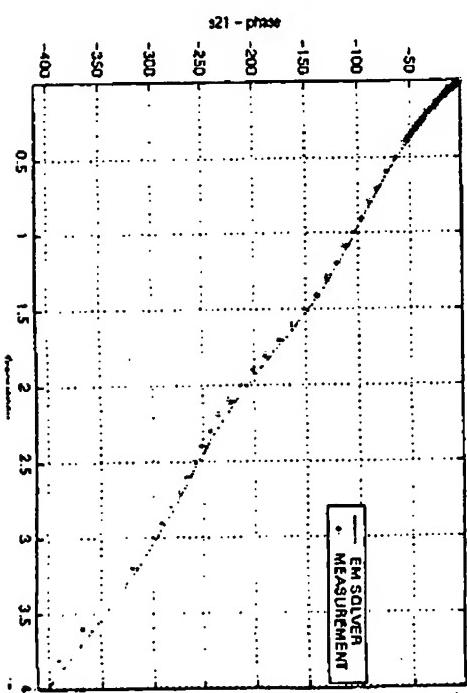
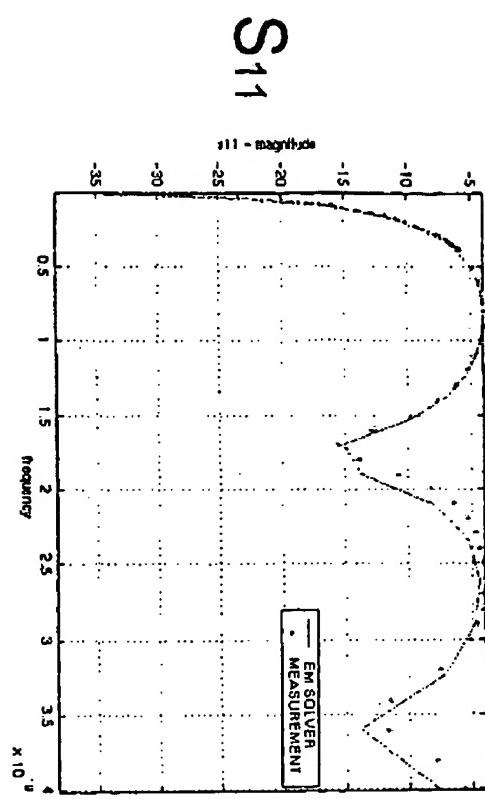
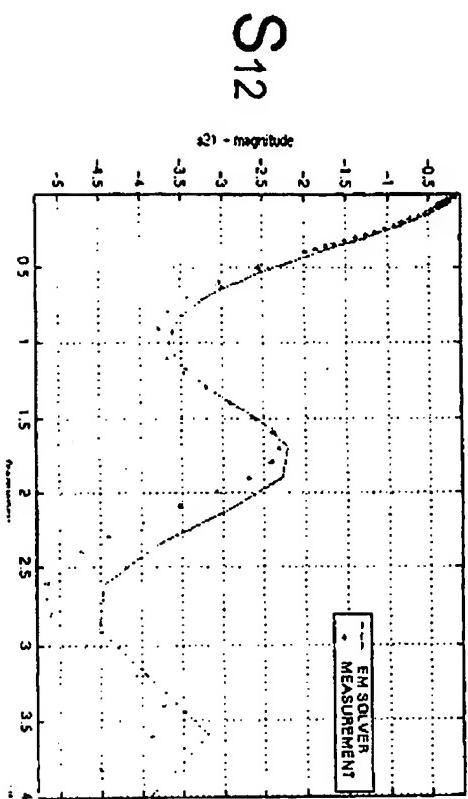
 S_{11}  S_{12} 

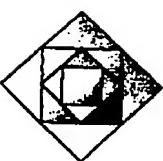


Hardware vs. Solver: Sample 3

$Z_0 \sim 25 \text{ [Ohm]}, \text{ Length} \sim 4[\text{mm}]$

Magnitude [db] Phase[degrees]

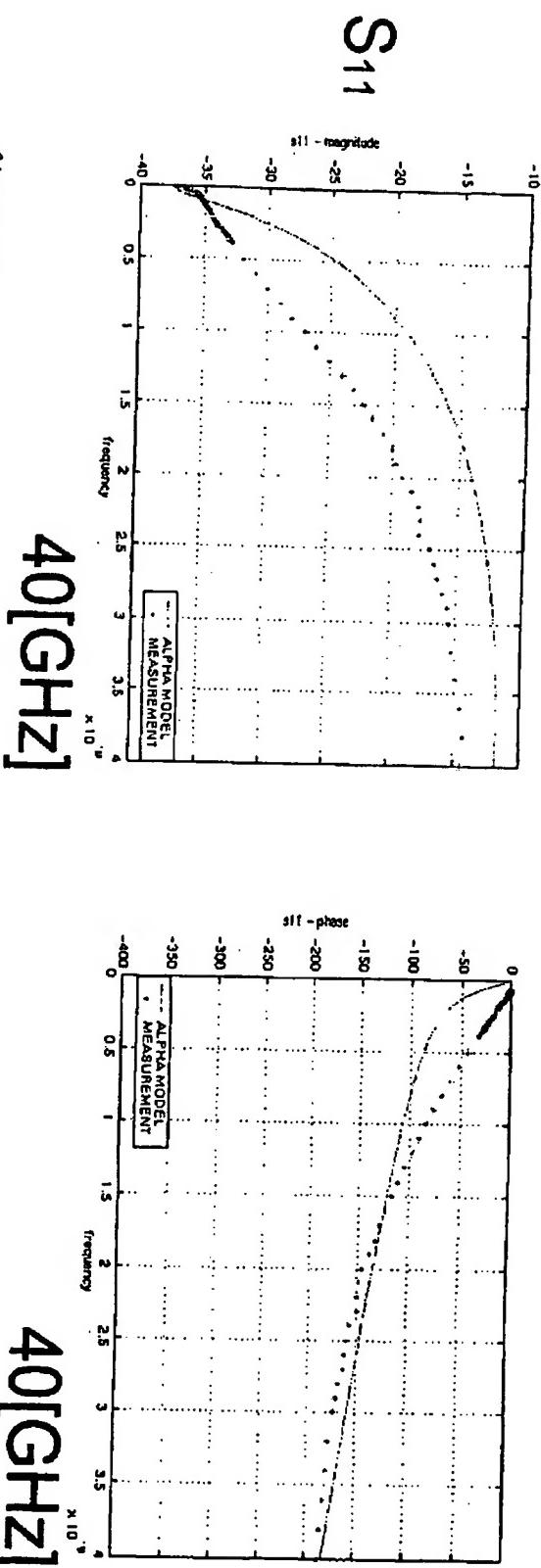




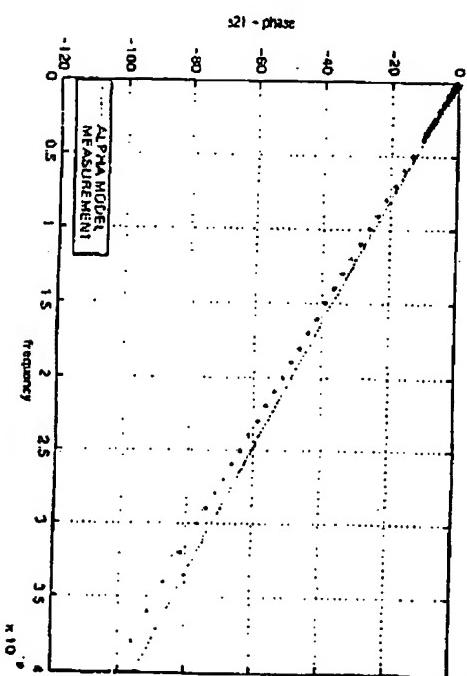
Alpha version results: Sample 1

$Z_0 \sim 50 \text{ [Ohm]}$, Length $\sim 1 \text{ [mm]}$

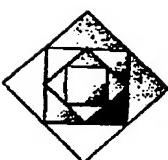
Magnitude [db] Phase[degrees]



40[GHz]



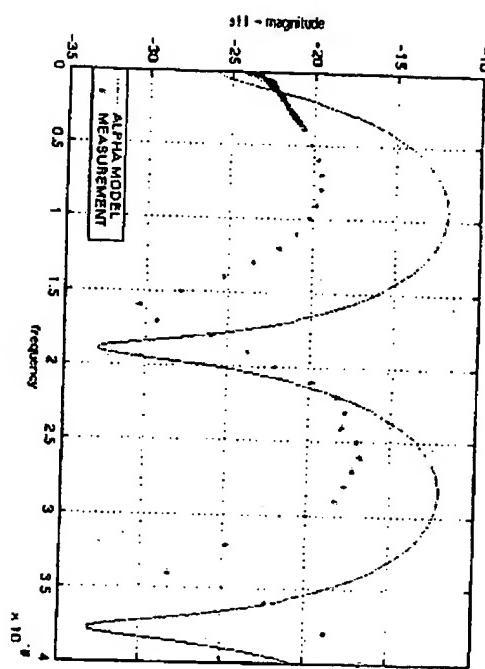
|3



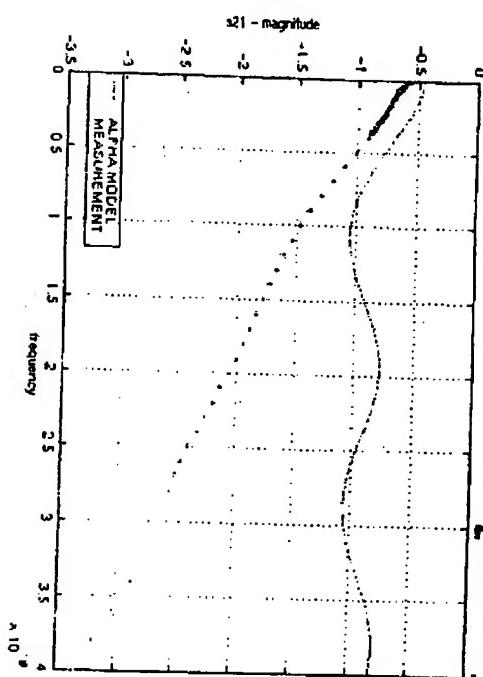
Alpha Version results: Sample 2

$Z_0 \sim 50 \text{ [Ohm]}, \text{ Length} \sim 4[\text{mm}]$

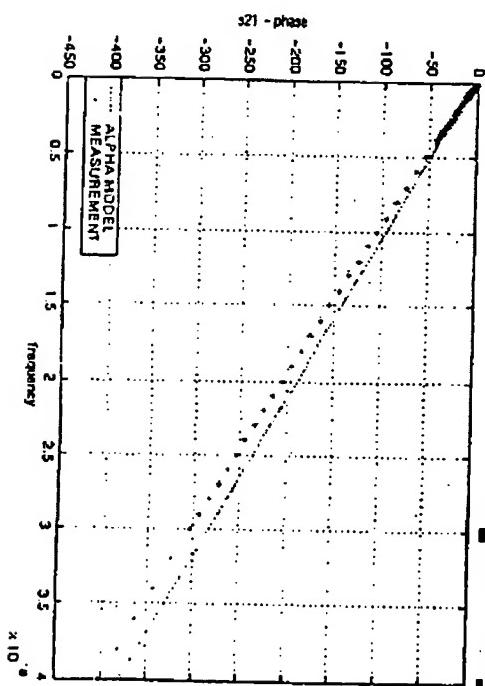
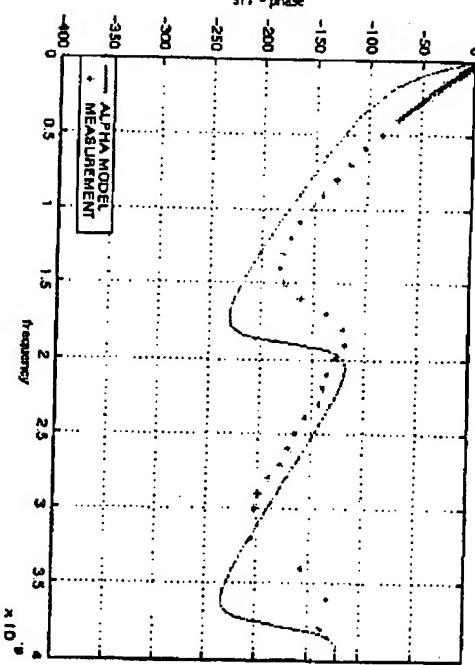
Magnitude [db] Phase[degrees]

 S_{11} 

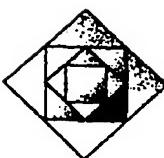
40[GHz]

 S_{21} 

40[GHz]

 $s11 - \text{phase}$ 

H



Alpha version results: Sample 3

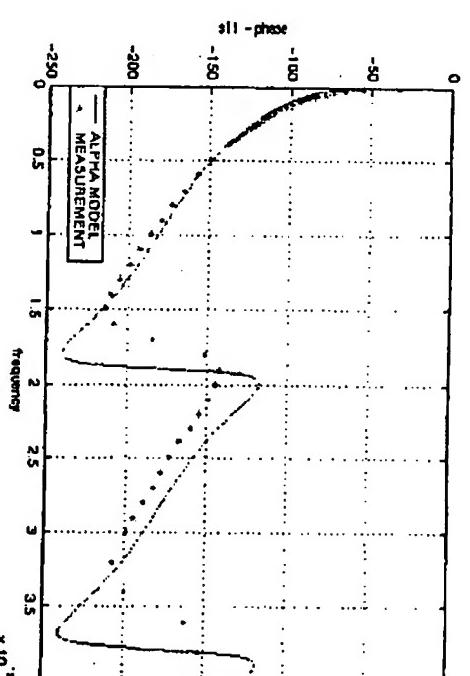
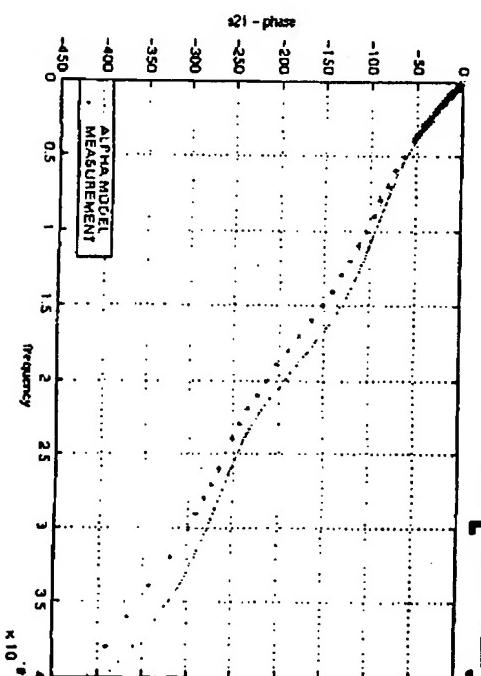
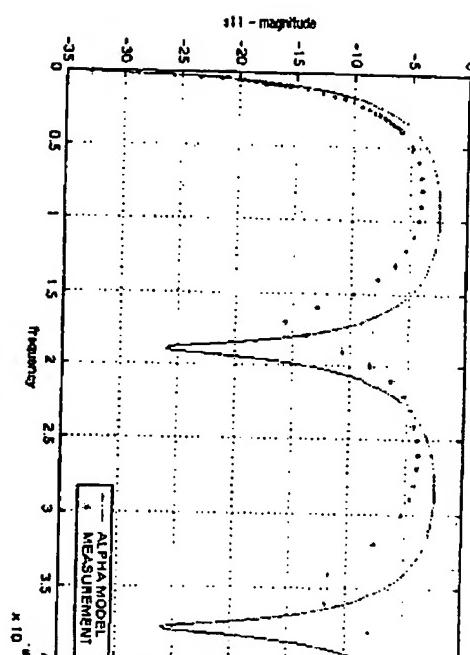
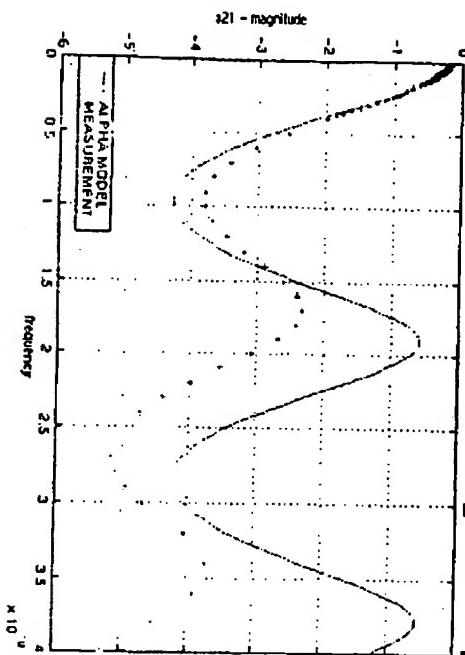
$Z_0 \sim 25 \text{ [Ohm]}, \text{ length} \sim 4 \text{ [mm]}$

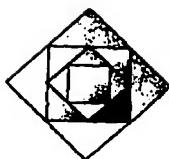
Magnitude [db] Phase[degrees]

 S_{12} S_{11}

40[GHz]

40[GHz]



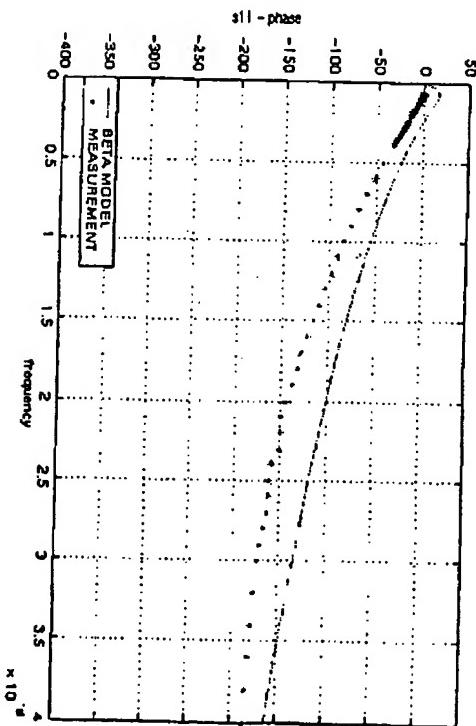
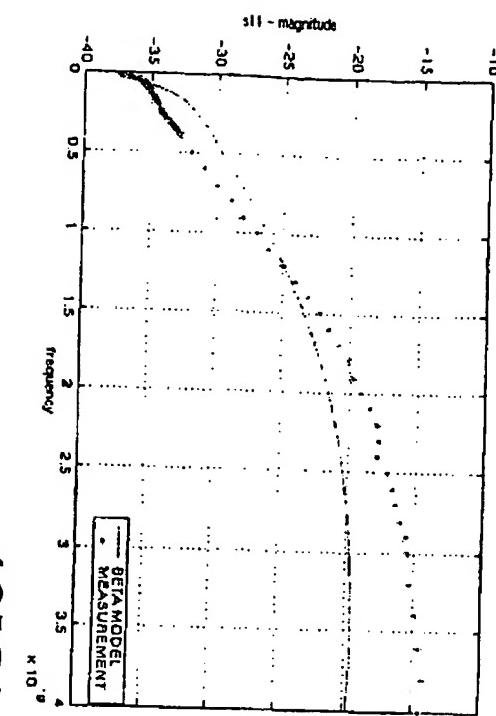


Beta version results: Sample 1

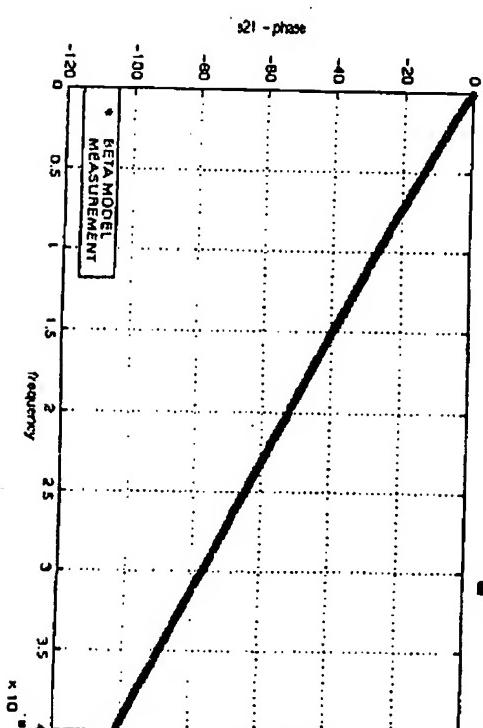
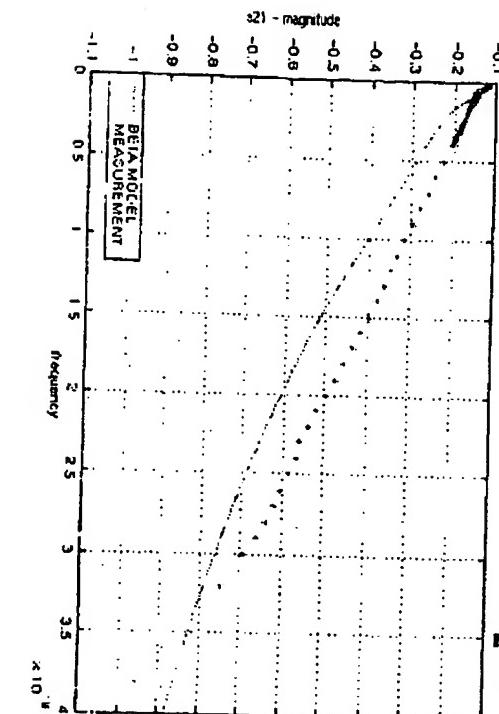
$Z_0 \sim 50[\Omega_m]$, length $\sim 1[m]$

Magnitude [db] Phase[degrees]

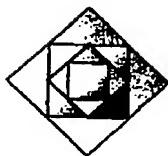
40[GHz]



40[GHz]



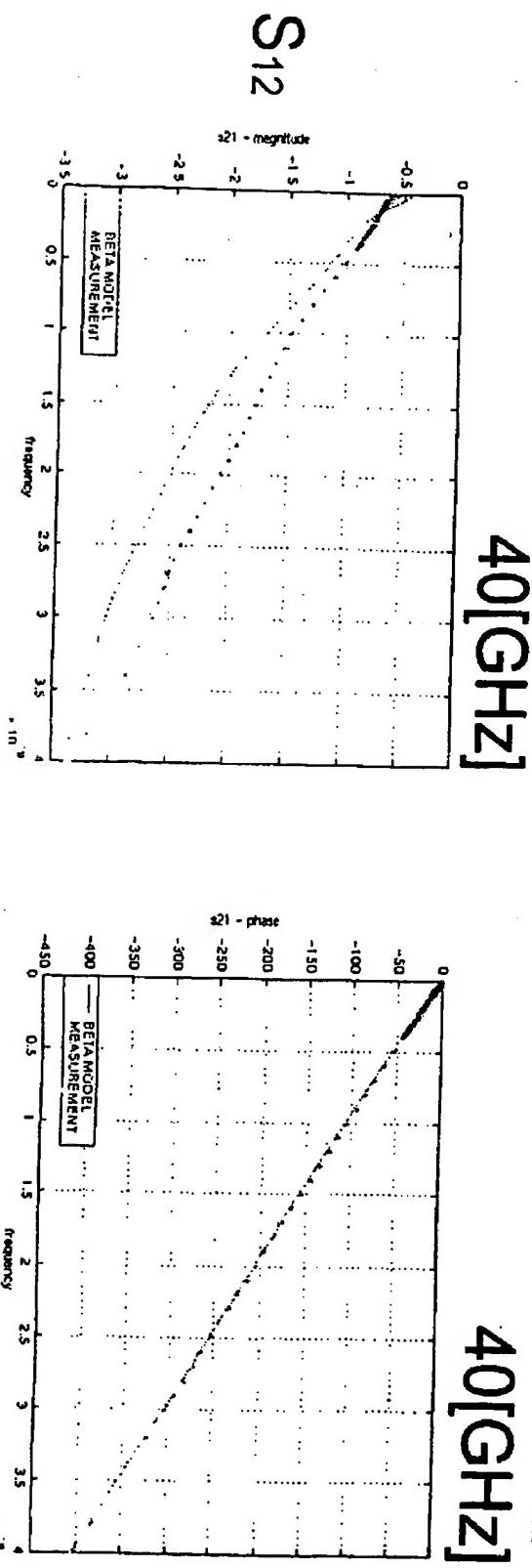
|b



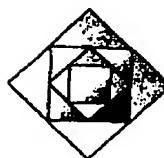
Beta version results: Sample 2

$Z_0 \sim 50[\Omega_m]$, Length $\sim 4[\text{mm}]$

Magnitude [db] Phase[degrees]



17



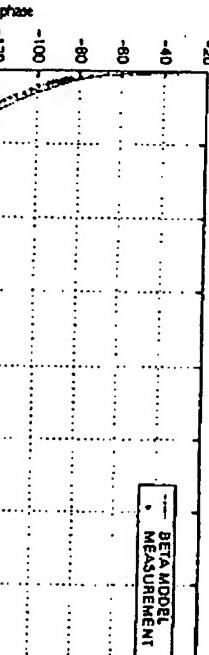
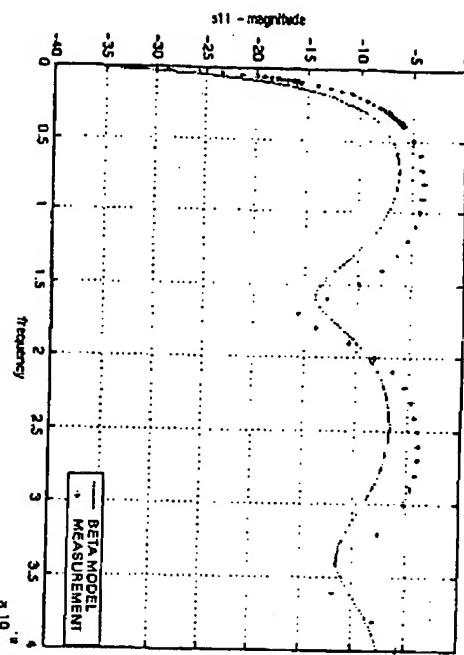
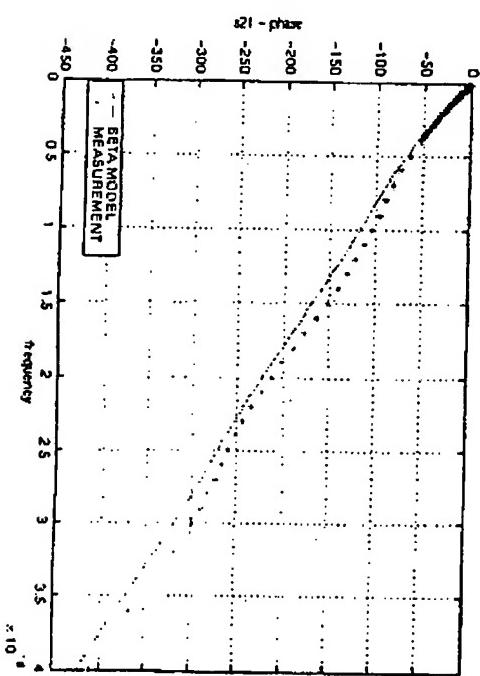
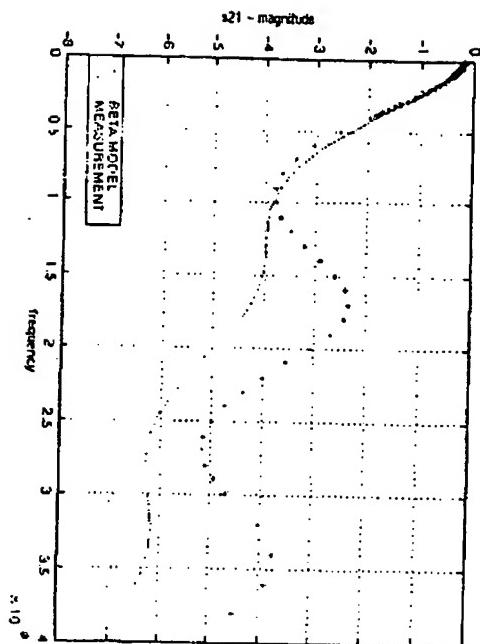
Beta version results: Sample 3

$Z_0 \sim 25 \text{ [Ohm]}, \text{Length} \sim 4[\text{mm}]$

Magnitude [db] Phase[degrees]

40[GHz]

40[GHz]

 S_{11}  S_{12} 

16